

IN THE CLAIMS:

Please amend the claims where indicated below:

B1  
1. (*currently amended*) A vertical cavity surface emitting laser, comprising:  
an active region further comprising at least one quantum well having a well depth of at least 40 meV, wherein said depth is defined as the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including GaAs barrier layers sandwiching said at least one quantum well; and GaAs confinement layers sandwiching said active region.

2. (*previously amended*) The vertical cavity surface emitting laser of claim 1 wherein said at least one quantum well is up to and including 50Å in thickness.

3. (*currently amended*) A vertical cavity surface emitting laser, comprising:  
an active region further comprising at least one quantum well having a well depth of at least 40 meV, wherein said depth is defined as the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including GaAsN barrier layers sandwiching said at least one quantum well; and AlGaAs confinement layers sandwiching said active region.

4. (*previously amended*) The vertical cavity surface emitting laser of claim 3 wherein said at least one quantum well is up to and including 50Å in thickness.

5. (*currently amended*) A vertical cavity surface emitting laser, comprising:  
an active region further comprising at least one quantum well having a well depth of at least 40 meV, wherein said depth is defined as the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including AlGaAs barrier layers sandwiching said at least one quantum well; and GaAsN confinement layers sandwiching said active region.

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6. (*previously amended*) The vertical cavity surface emitting laser of claim 5 wherein said at least one quantum well is up to and including 50Å in thickness.

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